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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	-
Number of I/O	77
Number of Gates	30000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p030-vq100

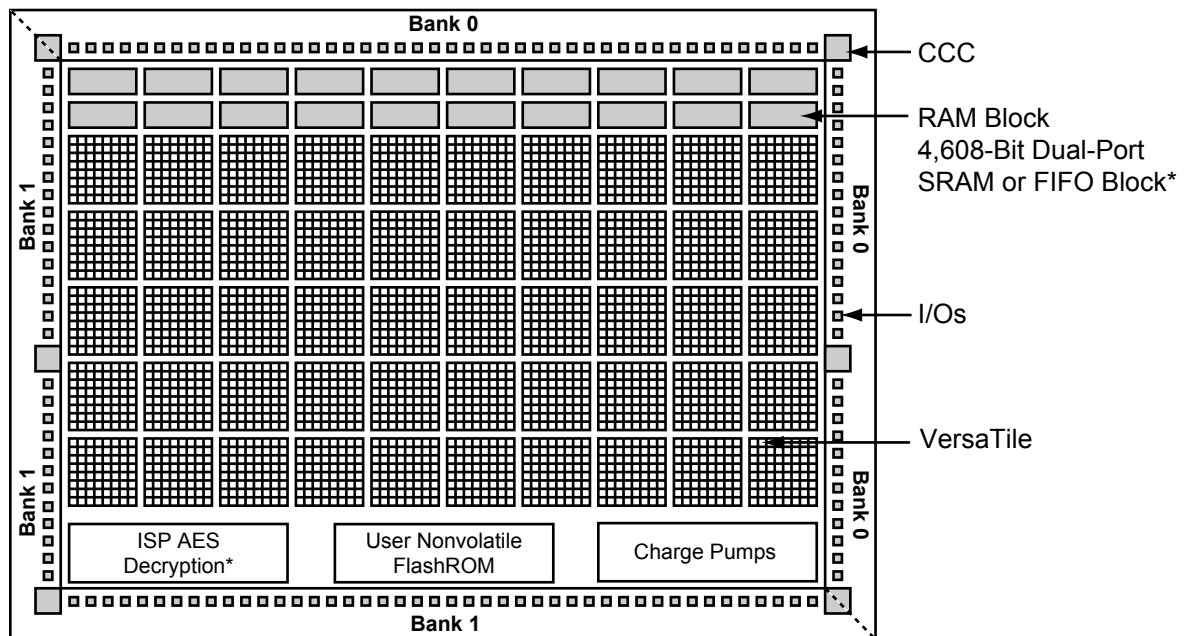
Advanced Flash Technology

The ProASIC3 family offers many benefits, including nonvolatility and reprogrammability through an advanced flash-based, 130-nm LVCMOS process with seven layers of metal. Standard CMOS design techniques are used to implement logic and control functions. The combination of fine granularity, enhanced flexible routing resources, and abundant flash switches allows for very high logic utilization without compromising device routability or performance. Logic functions within the device are interconnected through a four-level routing hierarchy.

Advanced Architecture

The proprietary ProASIC3 architecture provides granularity comparable to standard-cell ASICs. The ProASIC3 device consists of five distinct and programmable architectural features (Figure 1-1 and Figure 1-2 on page 1-4):

- FPGA VersaTiles
- Dedicated FlashROM
- Dedicated SRAM/FIFO memory[†]
- Extensive CCCs and PLLs[†]
- Advanced I/O structure



Note: *Not supported by A3P015 and A3P030 devices

Figure 1-1 • ProASIC3 Device Architecture Overview with Two I/O Banks (A3P015, A3P030, A3P060, and A3P125)

[†] The A3P015 and A3P030 do not support PLL or SRAM.

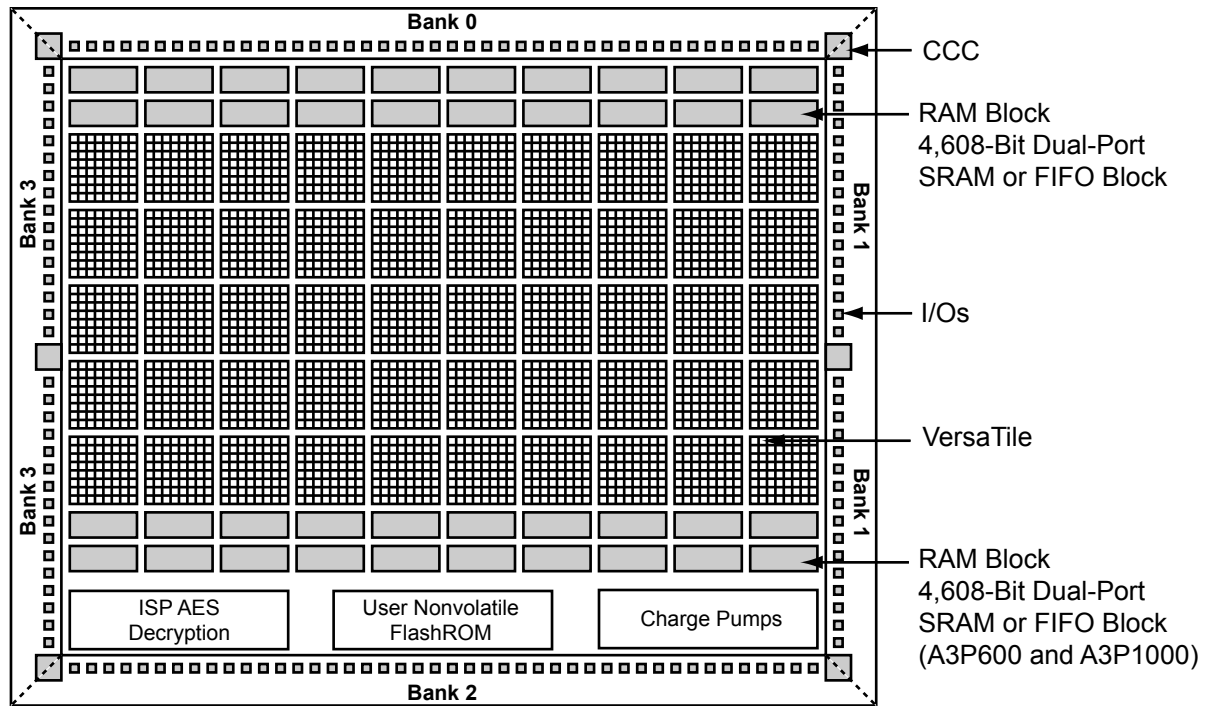


Figure 1-2 • ProASIC3 Device Architecture Overview with Four I/O Banks (A3P250, A3P600, and A3P1000)

The FPGA core consists of a sea of VersaTiles. Each VersaTile can be configured as a three-input logic function, a D-flip-flop (with or without enable), or a latch by programming the appropriate flash switch interconnections. The versatility of the ProASIC3 core tile as either a three-input lookup table (LUT) equivalent or as a D-flip-flop/latch with enable allows for efficient use of the FPGA fabric. The VersaTile capability is unique to the Microsemi ProASIC family of third-generation architecture flash FPGAs. VersaTiles are connected with any of the four levels of routing hierarchy. Flash switches are distributed throughout the device to provide nonvolatile, reconfigurable interconnect programming. Maximum core utilization is possible for virtually any design.

VersaTiles

The ProASIC3 core consists of VersaTiles, which have been enhanced beyond the ProASIC^{PLUS}® core tiles. The ProASIC3 VersaTile supports the following:

- All 3-input logic functions—LUT-3 equivalent
- Latch with clear or set
- D-flip-flop with clear or set
- Enable D-flip-flop with clear or set

Refer to [Figure 1-3](#) for VersaTile configurations.

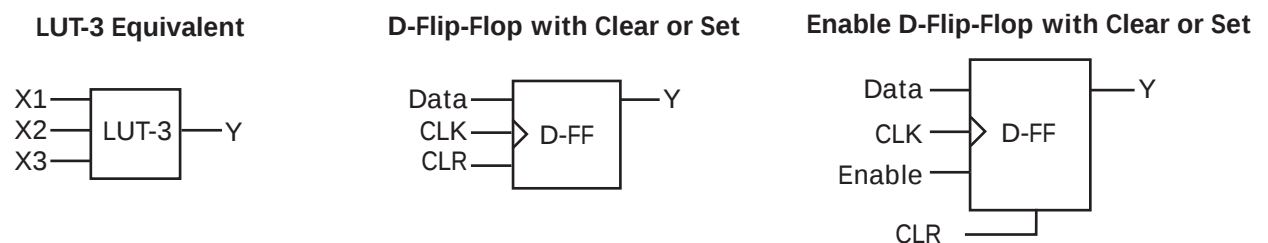


Figure 1-3 • VersaTile Configurations

Table 2-24 • Summary of I/O Timing Characteristics—Software Default Settings
 –2 Speed Grade, Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst Case $V_{CC} = 1.425\text{ V}$,
 Worst-Case V_{CCI} (per standard)
 Advanced I/O Banks

I/O Standard	Drive Strength	Equiv. Software Default Drive Strength Option ¹	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	t_{ZLS} (ns)	t_{ZHS} (ns)	Units
3.3 V LVTTTL / 3.3 V LVCMOS	12 mA	12 mA	High	35	–	0.45	2.64	0.03	0.76	0.32	2.69	2.11	2.40	2.68	4.36	3.78	ns
3.3 V LVCMOS Wide Range ²	100 μA	12 mA	High	35	–	0.45	4.08	0.03	0.76	0.32	4.08	3.20	3.71	4.14	6.61	5.74	ns
2.5 V LVCMOS	12 mA	12 mA	High	35	–	0.45	2.66	0.03	0.98	0.32	2.71	2.56	2.47	2.57	4.38	4.23	ns
1.8 V LVCMOS	12 mA	12 mA	High	35	–	0.45	2.64	0.03	0.91	0.32	2.69	2.27	2.76	3.05	4.36	3.94	ns
1.5 V LVCMOS	12 mA	12 mA	High	35	–	0.45	3.05	0.03	1.07	0.32	3.10	2.67	2.95	3.14	4.77	4.34	ns
3.3 V PCI	Per PCI spec	–	High	10	25 ⁴	0.45	2.00	0.03	0.65	0.32	2.04	1.46	2.40	2.68	3.71	3.13	ns
3.3 V PCI-X	Per PCI-X spec	–	High	10	25 ⁴	0.45	2.00	0.03	0.62	0.32	2.04	1.46	2.40	2.68	3.71	3.13	ns
LVDS	24 mA	–	High	–	–	0.45	1.37	0.03	1.20	–	–	–	–	–	–	–	ns
LVPECL	24 mA	–	High	–	–	0.45	1.34	0.03	1.05	–	–	–	–	–	–	–	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.
4. Resistance is used to measure I/O propagation delays as defined in PCI specifications. See [Figure 2-11 on page 2-64](#) for connectivity. This resistor is not required during normal operation.

Timing Characteristics

Table 2-41 • 3.3 V LVTTTL / 3.3 V LVCMOS High Slew

Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 3.0\text{ V}$
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	7.66	0.04	1.02	0.43	7.80	6.59	2.65	2.61	10.03	8.82	ns
	–1	0.56	6.51	0.04	0.86	0.36	6.63	5.60	2.25	2.22	8.54	7.51	ns
	–2	0.49	5.72	0.03	0.76	0.32	5.82	4.92	1.98	1.95	7.49	6.59	ns
4 mA	Std.	0.66	7.66	0.04	1.02	0.43	7.80	6.59	2.65	2.61	10.03	8.82	ns
	–1	0.56	6.51	0.04	0.86	0.36	6.63	5.60	2.25	2.22	8.54	7.51	ns
	–2	0.49	5.72	0.03	0.76	0.32	5.82	4.92	1.98	1.95	7.49	6.59	ns
6 mA	Std.	0.66	4.91	0.04	1.02	0.43	5.00	4.07	2.99	3.20	7.23	6.31	ns
	–1	0.56	4.17	0.04	0.86	0.36	4.25	3.46	2.54	2.73	6.15	5.36	ns
	–2	0.49	3.66	0.03	0.76	0.32	3.73	3.04	2.23	2.39	5.40	4.71	ns
8 mA	Std.	0.66	4.91	0.04	1.02	0.43	5.00	4.07	2.99	3.20	7.23	6.31	ns
	–1	0.56	4.17	0.04	0.86	0.36	4.25	3.46	2.54	2.73	6.15	5.36	ns
	–2	0.49	3.66	0.03	0.76	0.32	3.73	3.04	2.23	2.39	5.40	4.71	ns
12 mA	Std.	0.66	3.53	0.04	1.02	0.43	3.60	2.82	3.21	3.58	5.83	5.06	ns
	–1	0.56	3.00	0.04	0.86	0.36	3.06	2.40	2.73	3.05	4.96	4.30	ns
	–2	0.49	2.64	0.03	0.76	0.32	2.69	2.11	2.40	2.68	4.36	3.78	ns
16 mA	Std.	0.66	3.33	0.04	1.02	0.43	3.39	2.56	3.26	3.68	5.63	4.80	ns
	–1	0.56	2.83	0.04	0.86	0.36	2.89	2.18	2.77	3.13	4.79	4.08	ns
	–2	0.49	2.49	0.03	0.76	0.32	2.53	1.91	2.44	2.75	4.20	3.58	ns
24 mA	Std.	0.66	3.08	0.04	1.02	0.43	3.13	2.12	3.32	4.06	5.37	4.35	ns
	–1	0.56	2.62	0.04	0.86	0.36	2.66	1.80	2.83	3.45	4.57	3.70	ns
	–2	0.49	2.30	0.03	0.76	0.32	2.34	1.58	2.48	3.03	4.01	3.25	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-51 • 3.3 V LVTTTL / 3.3 V LVCMOS Low Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 3.0\text{ V}$

Applicable to Advanced I/O Banks

Drive Strength	Equiv. Software Default Drive Strength Option ¹	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 μA	2 mA	Std.	0.60	15.86	0.04	1.54	0.43	15.86	13.51	4.09	3.80	19.25	16.90	ns
		–1	0.51	13.49	0.04	1.31	0.36	13.49	11.49	3.48	3.23	16.38	14.38	ns
		–2	0.45	11.84	0.03	1.15	0.32	11.84	10.09	3.05	2.84	14.38	12.62	ns
100 μA	4 mA	Std.	0.60	11.25	0.04	1.54	0.43	11.25	9.54	4.61	4.70	14.64	12.93	ns
		–1	0.51	9.57	0.04	1.31	0.36	9.57	8.11	3.92	4.00	12.46	11.00	ns
		–2	0.45	8.40	0.03	1.15	0.32	8.40	7.12	3.44	3.51	10.93	9.66	ns
100 μA	6 mA	Std.	0.60	11.25	0.04	1.54	0.43	11.25	9.54	4.61	4.70	14.64	12.93	ns
		–1	0.51	9.57	0.04	1.31	0.36	9.57	8.11	3.92	4.00	12.46	11.00	ns
		–2	0.45	8.40	0.03	1.15	0.32	8.40	7.12	3.44	3.51	10.93	9.66	ns
100 μA	8 mA	Std.	0.60	8.63	0.04	1.54	0.43	8.63	7.39	4.96	5.28	12.02	10.79	ns
		–1	0.51	7.34	0.04	1.31	0.36	7.34	6.29	4.22	4.49	10.23	9.18	ns
		–2	0.45	6.44	0.03	1.15	0.32	6.44	5.52	3.70	3.94	8.98	8.06	ns
100 μA	16 mA	Std.	0.60	8.05	0.04	1.54	0.43	8.05	6.93	5.03	5.43	11.44	10.32	ns
		–1	0.51	6.85	0.04	1.31	0.36	6.85	5.90	4.28	4.62	9.74	8.78	ns
		–2	0.45	6.01	0.03	1.15	0.32	6.01	5.18	3.76	4.06	8.55	7.71	ns
100 μA	24 mA	Std.	0.60	7.50	0.04	1.54	0.43	7.50	6.90	5.13	6.00	10.89	10.29	ns
		–1	0.51	6.38	0.04	1.31	0.36	6.38	5.87	4.36	5.11	9.27	8.76	ns
		–2	0.45	5.60	0.03	1.15	0.32	5.60	5.15	3.83	4.48	8.13	7.69	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-52 • 3.3 V LVTTTL / 3.3 V LVCMOS High Slew
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 3.0\text{ V}$
Applicable to Standard Plus I/O Banks

Drive Strength	Equiv. Software Default Drive Strength Option ¹	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 μA	2 mA	Std.	0.60	11.14	0.04	1.52	0.43	11.14	9.54	3.51	3.61	14.53	12.94	ns
		–1	0.51	9.48	0.04	1.29	0.36	9.48	8.12	2.99	3.07	12.36	11.00	ns
		–2	0.45	8.32	0.03	1.14	0.32	8.32	7.13	2.62	2.70	10.85	9.66	ns
100 μA	4 mA	Std.	0.60	6.96	0.04	1.52	0.43	6.96	5.79	3.99	4.45	10.35	9.19	ns
		–1	0.51	5.92	0.04	1.29	0.36	5.92	4.93	3.39	3.78	8.81	7.82	ns
		–2	0.45	5.20	0.03	1.14	0.32	5.20	4.33	2.98	3.32	7.73	6.86	ns
100 μA	6 mA	Std.	0.60	6.96	0.04	1.52	0.43	6.96	5.79	3.99	4.45	10.35	9.19	ns
		–1	0.51	5.92	0.04	1.29	0.36	5.92	4.93	3.39	3.78	8.81	7.82	ns
		–2	0.45	5.20	0.03	1.14	0.32	5.20	4.33	2.98	3.32	7.73	6.86	ns
100 μA	8 mA	Std.	0.60	4.89	0.04	1.52	0.43	4.89	3.92	4.31	4.98	8.28	7.32	ns
		–1	0.51	4.16	0.04	1.29	0.36	4.16	3.34	3.67	4.24	7.04	6.22	ns
		–2	0.45	3.65	0.03	1.14	0.32	3.65	2.93	3.22	3.72	6.18	5.46	ns
100 μA	16 mA	Std.	0.60	4.89	0.04	1.52	0.43	4.89	3.92	4.31	4.98	8.28	7.32	ns
		–1	0.51	4.16	0.04	1.29	0.36	4.16	3.34	3.67	4.24	7.04	6.22	ns
		–2	0.45	3.65	0.03	1.14	0.32	3.65	2.93	3.22	3.72	6.18	5.46	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. Software default selection highlighted in gray.
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-71 • 1.8 V LVCMOS Low Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 1.7\text{ V}$
 Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	15.53	0.04	1.22	0.43	14.11	15.53	2.78	1.60	16.35	17.77	ns
	–1	0.56	13.21	0.04	1.04	0.36	12.01	13.21	2.36	1.36	13.91	15.11	ns
	–2	0.49	11.60	0.03	0.91	0.32	10.54	11.60	2.07	1.19	12.21	13.27	ns
4 mA	Std.	0.66	10.48	0.04	1.22	0.43	10.41	10.48	3.23	2.73	12.65	12.71	ns
	–1	0.56	8.91	0.04	1.04	0.36	8.86	8.91	2.75	2.33	10.76	10.81	ns
	–2	0.49	7.82	0.03	0.91	0.32	7.77	7.82	2.41	2.04	9.44	9.49	ns
6 mA	Std.	0.66	8.05	0.04	1.22	0.43	8.20	7.84	3.54	3.27	10.43	10.08	ns
	–1	0.56	6.85	0.04	1.04	0.36	6.97	6.67	3.01	2.78	8.88	8.57	ns
	–2	0.49	6.01	0.03	0.91	0.32	6.12	5.86	2.64	2.44	7.79	7.53	ns
8 mA	Std.	0.66	7.50	0.04	1.22	0.43	7.64	7.30	3.61	3.41	9.88	9.53	ns
	–1	0.56	6.38	0.04	1.04	0.36	6.50	6.21	3.07	2.90	8.40	8.11	ns
	–2	0.49	5.60	0.03	0.91	0.32	5.71	5.45	2.69	2.55	7.38	7.12	ns
12 mA	Std.	0.66	7.29	0.04	1.22	0.43	7.23	7.29	3.71	3.95	9.47	9.53	ns
	–1	0.56	6.20	0.04	1.04	0.36	6.15	6.20	3.15	3.36	8.06	8.11	ns
	–2	0.49	5.45	0.03	0.91	0.32	5.40	5.45	2.77	2.95	7.07	7.12	ns
16 mA	Std.	0.66	7.29	0.04	1.22	0.43	7.23	7.29	3.71	3.95	9.47	9.53	ns
	–1	0.56	6.20	0.04	1.04	0.36	6.15	6.20	3.15	3.36	8.06	8.11	ns
	–2	0.49	5.45	0.03	0.91	0.32	5.40	5.45	2.77	2.95	7.07	7.12	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Output Register

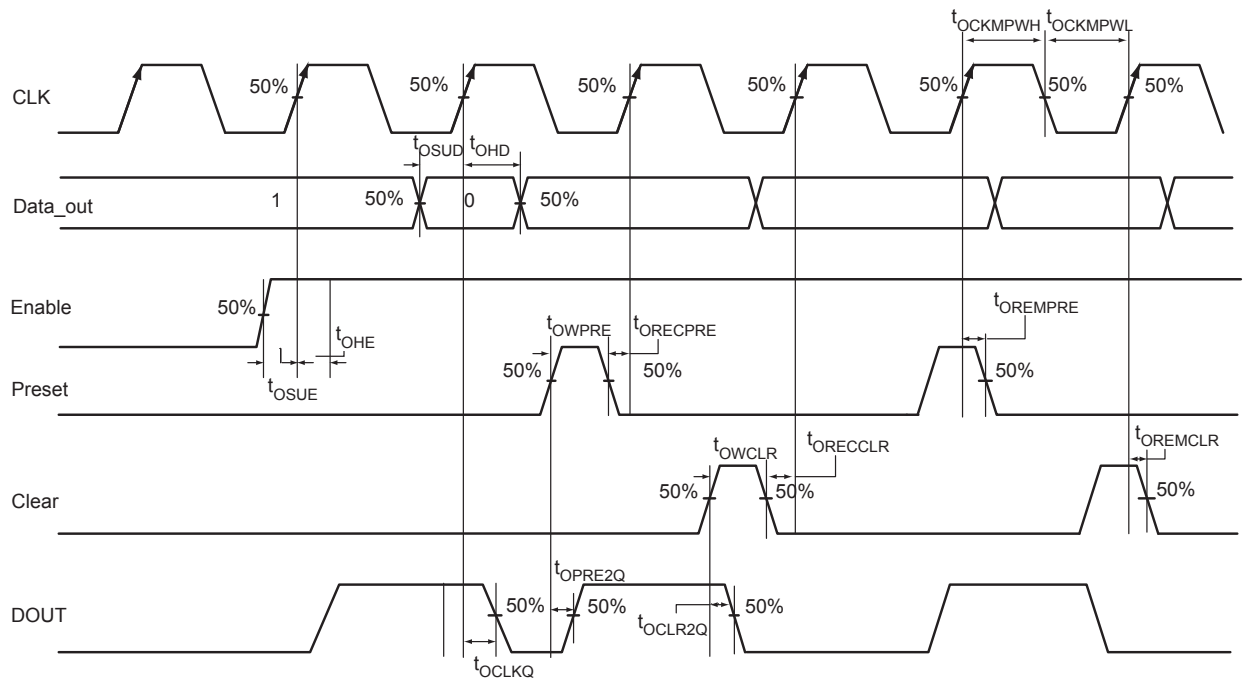


Figure 2-18 • Output Register Timing Diagram

Timing Characteristics

Table 2-99 • Output Data Register Propagation Delays

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
t_{OCLKQ}	Clock-to-Q of the Output Data Register	0.59	0.67	0.79	ns
t_{OSUD}	Data Setup Time for the Output Data Register	0.31	0.36	0.42	ns
t_{OHD}	Data Hold Time for the Output Data Register	0.00	0.00	0.00	ns
t_{OSUE}	Enable Setup Time for the Output Data Register	0.44	0.50	0.59	ns
t_{OHE}	Enable Hold Time for the Output Data Register	0.00	0.00	0.00	ns
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	0.80	0.91	1.07	ns
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	0.80	0.91	1.07	ns
t_{OEMCLR}	Asynchronous Clear Removal Time for the Output Data Register	0.00	0.00	0.00	ns
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	0.22	0.25	0.30	ns
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	0.00	0.00	0.00	ns
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	0.22	0.25	0.30	ns
t_{OWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Data Register	0.22	0.25	0.30	ns
t_{OWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Data Register	0.22	0.25	0.30	ns
$t_{OCKMPWH}$	Clock Minimum Pulse Width High for the Output Data Register	0.36	0.41	0.48	ns
$t_{OCKMPWL}$	Clock Minimum Pulse Width Low for the Output Data Register	0.32	0.37	0.43	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Timing Characteristics

Table 2-100 • Output Enable Register Propagation Delays
 Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	0.59	0.67	0.79	ns
t_{OESUD}	Data Setup Time for the Output Enable Register	0.31	0.36	0.42	ns
t_{OEHD}	Data Hold Time for the Output Enable Register	0.00	0.00	0.00	ns
t_{OESUE}	Enable Setup Time for the Output Enable Register	0.44	0.50	0.58	ns
t_{OEHE}	Enable Hold Time for the Output Enable Register	0.00	0.00	0.00	ns
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	0.67	0.76	0.89	ns
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	0.67	0.76	0.89	ns
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	0.00	0.00	0.00	ns
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	0.22	0.25	0.30	ns
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	0.00	0.00	0.00	ns
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	0.22	0.25	0.30	ns
$t_{OEWCCLR}$	Asynchronous Clear Minimum Pulse Width for the Output Enable Register	0.22	0.25	0.30	ns
t_{OEWPPE}	Asynchronous Preset Minimum Pulse Width for the Output Enable Register	0.22	0.25	0.30	ns
$t_{OECKMPWH}$	Clock Minimum Pulse Width High for the Output Enable Register	0.36	0.41	0.48	ns
$t_{OECKMPWL}$	Clock Minimum Pulse Width Low for the Output Enable Register	0.32	0.37	0.43	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

DDR Module Specifications

Input DDR Module

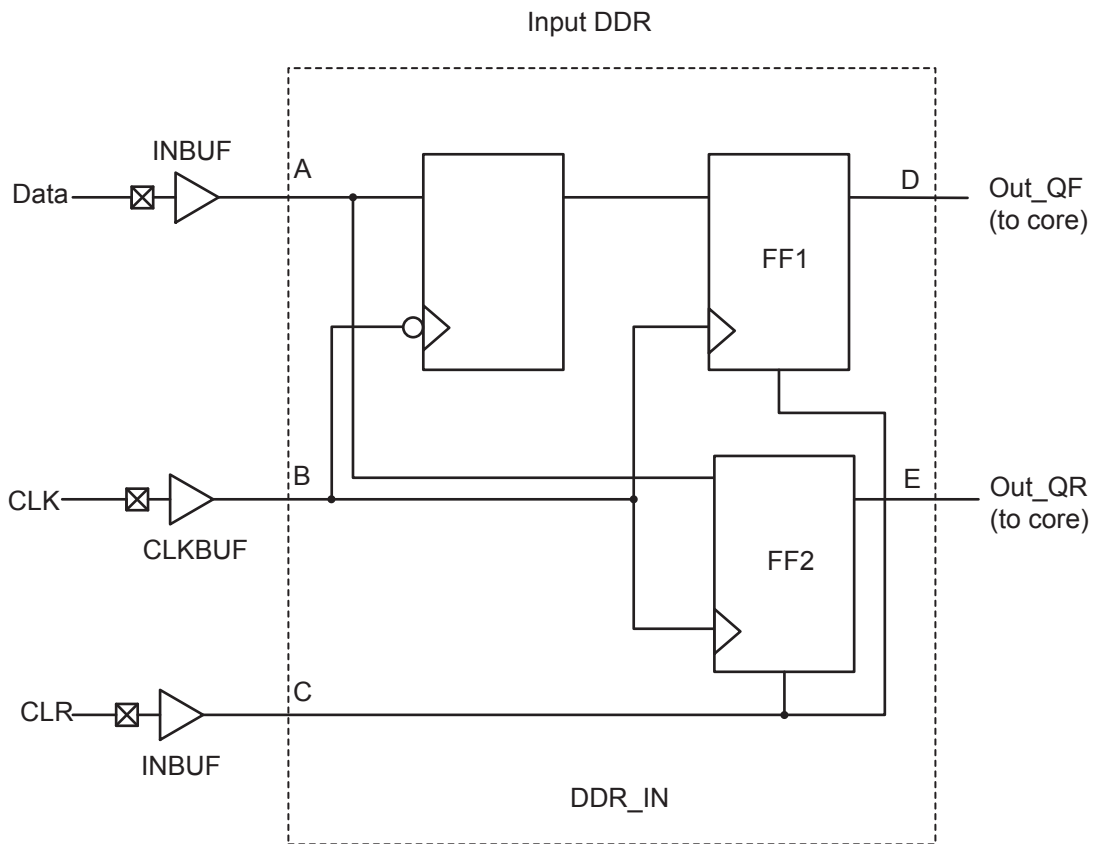


Figure 2-20 • Input DDR Timing Model

Table 2-101 • Parameter Definitions

Parameter Name	Parameter Definition	Measuring Nodes (from, to)
t_{DDRCLKQ1}	Clock-to-Out Out_QR	B, D
t_{DDRCLKQ2}	Clock-to-Out Out_QF	B, E
t_{DDRISUD}	Data Setup Time of DDR input	A, B
$t_{\text{DDR IHD}}$	Data Hold Time of DDR input	A, B
$t_{\text{DDRICLR2Q1}}$	Clear-to-Out Out_QR	C, D
$t_{\text{DDRICLR2Q2}}$	Clear-to-Out Out_QF	C, E
$t_{\text{DDRIREMCLR}}$	Clear Removal	C, B
$t_{\text{DDRIRECCLR}}$	Clear Recovery	C, B

Timing Characteristics

Table 2-105 • Combinatorial Cell Propagation Delays

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Combinatorial Cell	Equation	Parameter	-2	-1	Std.	Units
INV	$Y = !A$	t_{PD}	0.40	0.46	0.54	ns
AND2	$Y = A \cdot B$	t_{PD}	0.47	0.54	0.63	ns
NAND2	$Y = !(A \cdot B)$	t_{PD}	0.47	0.54	0.63	ns
OR2	$Y = A + B$	t_{PD}	0.49	0.55	0.65	ns
NOR2	$Y = !(A + B)$	t_{PD}	0.49	0.55	0.65	ns
XOR2	$Y = A \oplus B$	t_{PD}	0.74	0.84	0.99	ns
MAJ3	$Y = \text{MAJ}(A, B, C)$	t_{PD}	0.70	0.79	0.93	ns
XOR3	$Y = A \oplus B \oplus C$	t_{PD}	0.87	1.00	1.17	ns
MUX2	$Y = A !S + B S$	t_{PD}	0.51	0.58	0.68	ns
AND3	$Y = A \cdot B \cdot C$	t_{PD}	0.56	0.64	0.75	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

VersaTile Specifications as a Sequential Module

The ProASIC3 library offers a wide variety of sequential cells, including flip-flops and latches. Each has a data input and optional enable, clear, or preset. In this section, timing characteristics are presented for a representative sample from the library. For more details, refer to the [Fusion](#), [IGLOO/e](#), and [ProASIC3/E Macro Library Guide](#).

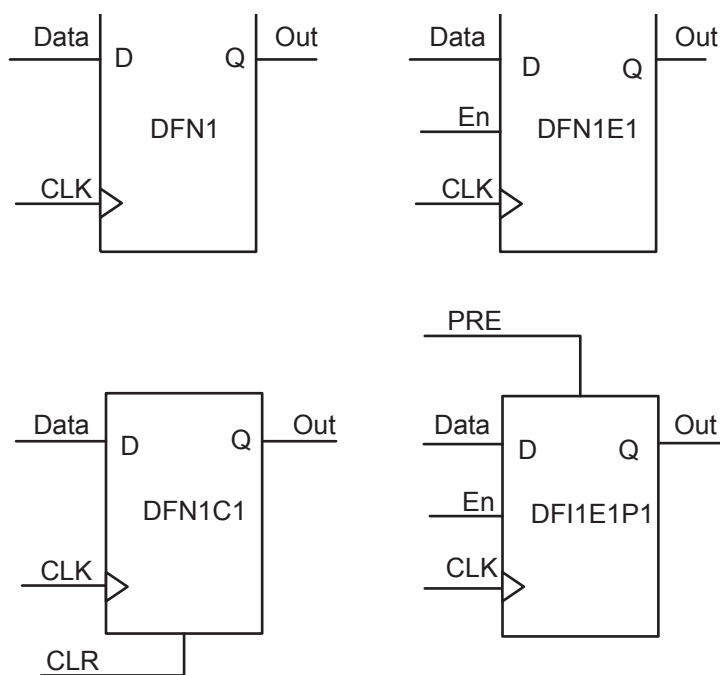


Figure 2-26 • Sample of Sequential Cells

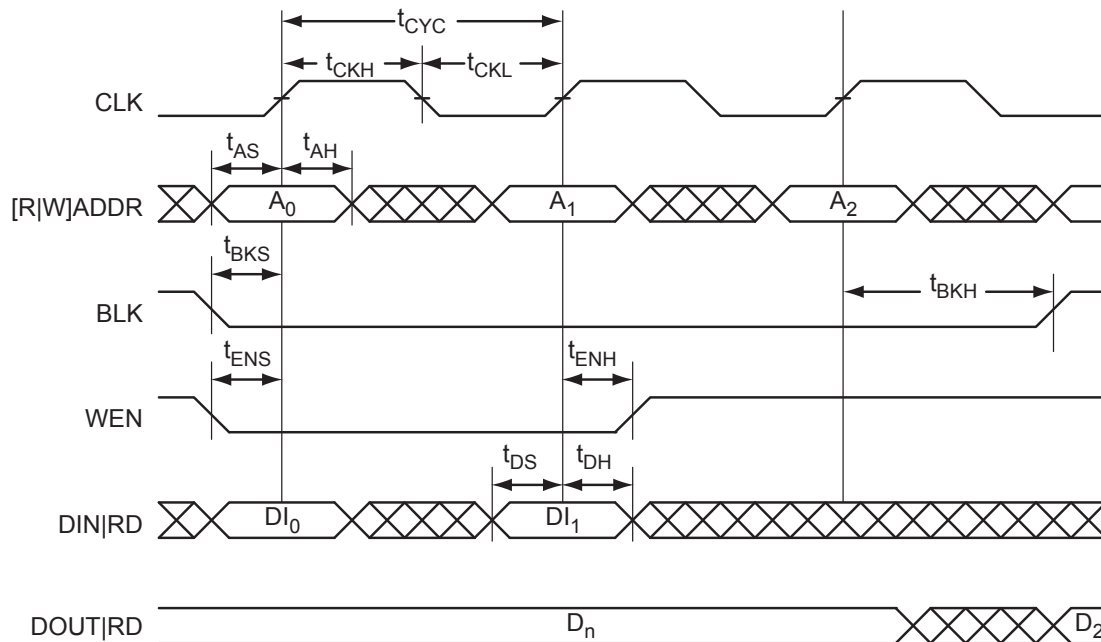


Figure 2-33 • RAM Write, Output Retained. Applicable to Both RAM4K9 and RAM512x18.

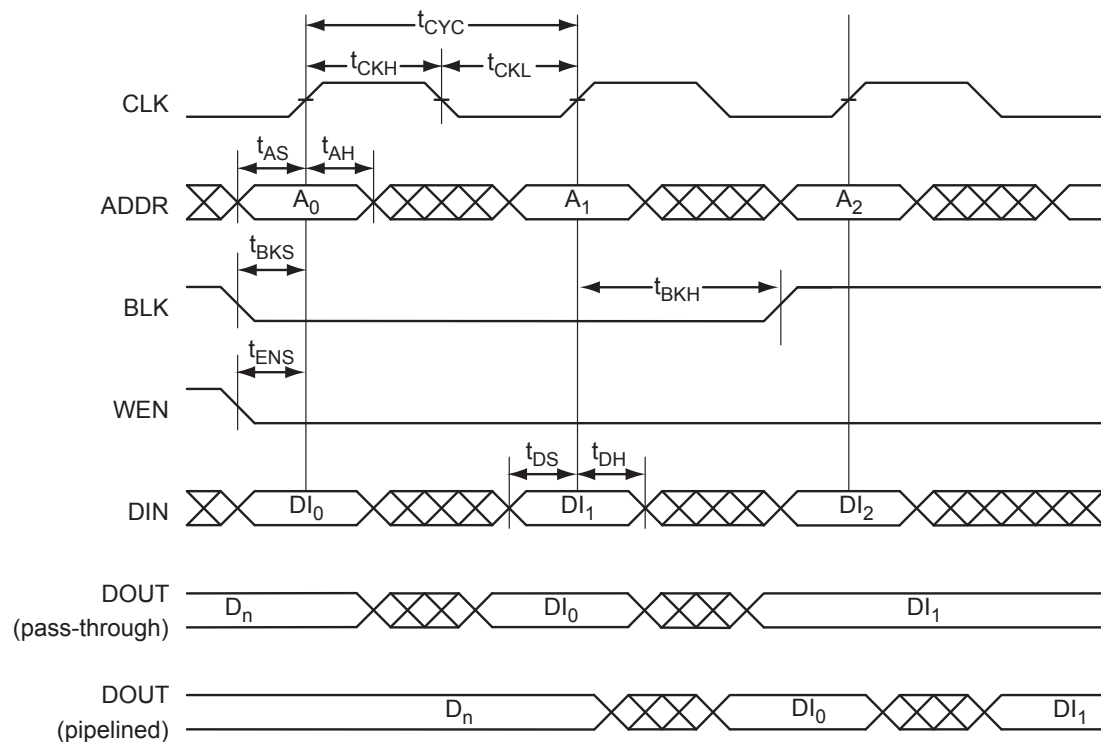


Figure 2-34 • RAM Write, Output as Write Data (WMODE = 1). Applicable to RAM4K9 Only.

JTAG 1532 Characteristics

JTAG timing delays do not include JTAG I/Os. To obtain complete JTAG timing, add I/O buffer delays to the corresponding standard selected; refer to the I/O timing characteristics in the "User I/O Characteristics" section on page 2-15 for more details.

Timing Characteristics

Table 2-125 • JTAG 1532

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
t_{DISU}	Test Data Input Setup Time	0.50	0.57	0.67	ns
t_{DIHD}	Test Data Input Hold Time	1.00	1.13	1.33	ns
t_{TMSSU}	Test Mode Select Setup Time	0.50	0.57	0.67	ns
t_{TMDHD}	Test Mode Select Hold Time	1.00	1.13	1.33	ns
t_{TCK2Q}	Clock to Q (data out)	6.00	6.80	8.00	ns
t_{RSTB2Q}	Reset to Q (data out)	20.00	22.67	26.67	ns
F_{TCKMAX}	TCK Maximum Frequency	25.00	22.00	19.00	MHz
$t_{TRSTREM}$	ResetB Removal Time	0.00	0.00	0.00	ns
$t_{TRSTREC}$	ResetB Recovery Time	0.20	0.23	0.27	ns
$t_{TRSTMPW}$	ResetB Minimum Pulse	TBD	TBD	TBD	ns

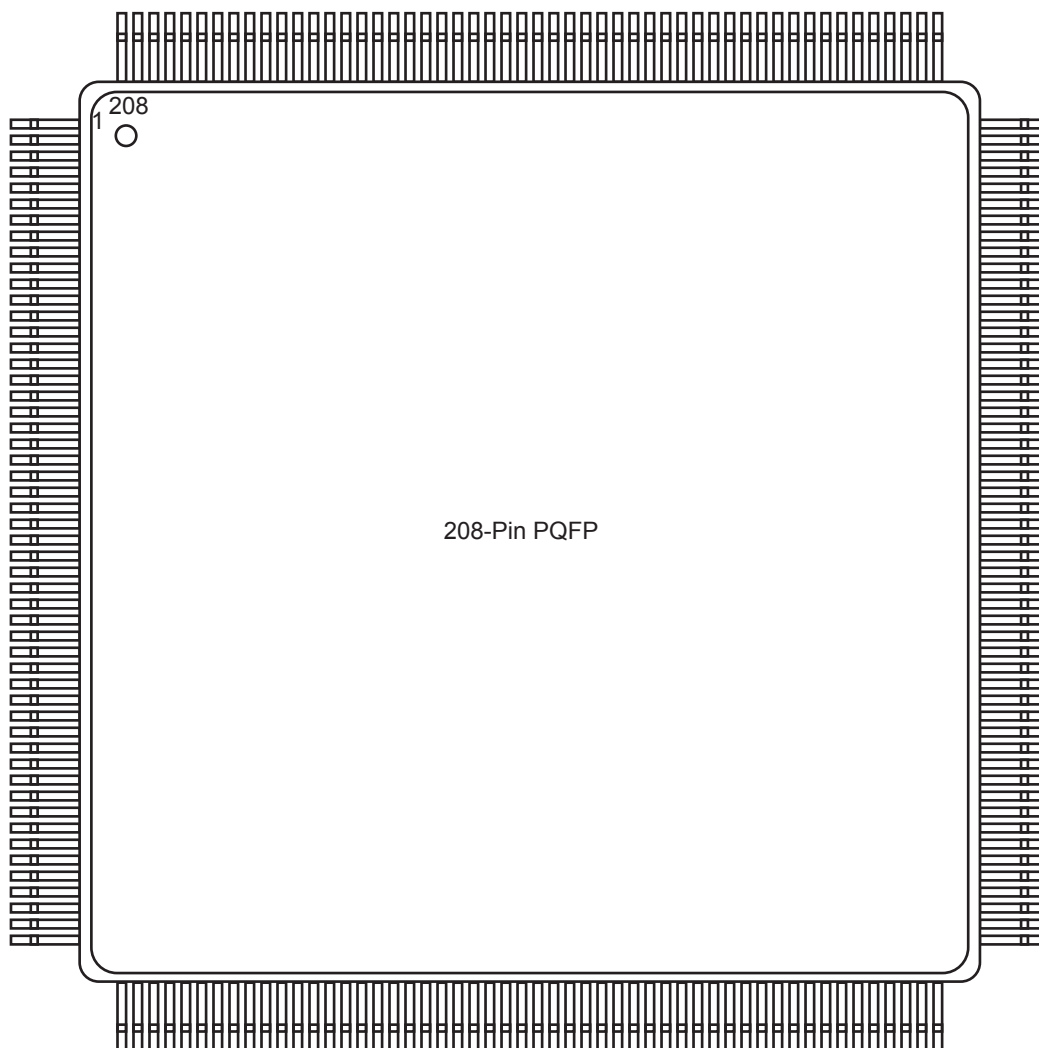
Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

CS121	
Pin Number	A3P060 Function
A1	GNDQ
A2	IO01RSB0
A3	GAA1/IO03RSB0
A4	GAC1/IO07RSB0
A5	IO15RSB0
A6	IO13RSB0
A7	IO17RSB0
A8	GBB1/IO22RSB0
A9	GBA1/IO24RSB0
A10	GNDQ
A11	VMV0
B1	GAA2/IO95RSB1
B2	IO00RSB0
B3	GAA0/IO02RSB0
B4	GAC0/IO06RSB0
B5	IO08RSB0
B6	IO12RSB0
B7	IO16RSB0
B8	GBC1/IO20RSB0
B9	GBB0/IO21RSB0
B10	GBB2/IO27RSB0
B11	GBA2/IO25RSB0
C1	IO89RSB1
C2	GAC2/IO91RSB1
C3	GAB1/IO05RSB0
C4	GAB0/IO04RSB0
C5	IO09RSB0
C6	IO14RSB0
C7	GBA0/IO23RSB0
C8	GBC0/IO19RSB0
C9	IO26RSB0
C10	IO28RSB0
C11	GBC2/IO29RSB0
D1	IO88RSB1
D2	IO90RSB1
D3	GAB2/IO93RSB1

CS121	
Pin Number	A3P060 Function
D4	IO10RSB0
D5	IO11RSB0
D6	IO18RSB0
D7	IO32RSB0
D8	IO31RSB0
D9	GCA2/IO41RSB0
D10	IO30RSB0
D11	IO33RSB0
E1	IO87RSB1
E2	GFC0/IO85RSB1
E3	IO92RSB1
E4	IO94RSB1
E5	VCC
E6	VCCIB0
E7	GND
E8	GCC0/IO36RSB0
E9	IO34RSB0
E10	GCB1/IO37RSB0
E11	GCC1/IO35RSB0
F1	VCOMPLF
F2	GFB0/IO83RSB1
F3	GFA0/IO82RSB1
F4	GFC1/IO86RSB1
F5	VCCIB1
F6	VCC
F7	VCCIB0
F8	GCB2/IO42RSB0
F9	GCC2/IO43RSB0
F10	GCB0/IO38RSB0
F11	GCA1/IO39RSB0
G1	VCCPLF
G2	GFB2/IO79RSB1
G3	GFA1/IO81RSB1
G4	GFB1/IO84RSB1
G5	GND
G6	VCCIB1

CS121	
Pin Number	A3P060 Function
G7	VCC
G8	GDC0/IO46RSB0
G9	GDA1/IO49RSB0
G10	GDB0/IO48RSB0
G11	GCA0/IO40RSB0
H1	IO75RSB1
H2	IO76RSB1
H3	GFC2/IO78RSB1
H4	GFA2/IO80RSB1
H5	IO77RSB1
H6	GEC2/IO66RSB1
H7	IO54RSB1
H8	GDC2/IO53RSB1
H9	VJTAG
H10	TRST
H11	IO44RSB0
J1	GEC1/IO74RSB1
J2	GEC0/IO73RSB1
J3	GEB1/IO72RSB1
J4	GEA0/IO69RSB1
J5	GEB2/IO67RSB1
J6	IO62RSB1
J7	GDA2/IO51RSB1
J8	GDB2/IO52RSB1
J9	TDI
J10	TDO
J11	GDC1/IO45RSB0
K1	GEB0/IO71RSB1
K2	GFA1/IO70RSB1
K3	GFA2/IO68RSB1
K4	IO64RSB1
K5	IO60RSB1
K6	IO59RSB1
K7	IO56RSB1
K8	TCK
K9	TMS

PQ208 – Top View



Note

For more information on package drawings, see [PD3068: Package Mechanical Drawings](#).

PQ208	
Pin Number	A3P250 Function
1	GND
2	GAA2/IO118UDB3
3	IO118VDB3
4	GAB2/IO117UDB3
5	IO117VDB3
6	GAC2/IO116UDB3
7	IO116VDB3
8	IO115UDB3
9	IO115VDB3
10	IO114UDB3
11	IO114VDB3
12	IO113PDB3
13	IO113NDB3
14	IO112PDB3
15	IO112NDB3
16	VCC
17	GND
18	VCCIB3
19	IO111PDB3
20	IO111NDB3
21	GFC1/IO110PDB3
22	GFC0/IO110NDB3
23	GFB1/IO109PDB3
24	GFB0/IO109NDB3
25	VCOMPLF
26	GFA0/IO108NPB3
27	VCCPLF
28	GFA1/IO108PPB3
29	GND
30	GFA2/IO107PDB3
31	IO107NDB3
32	GFB2/IO106PDB3
33	IO106NDB3
34	GFC2/IO105PDB3
35	IO105NDB3
36	NC

PQ208	
Pin Number	A3P250 Function
37	IO104PDB3
38	IO104NDB3
39	IO103PSB3
40	VCCIB3
41	GND
42	IO101PDB3
43	IO101NDB3
44	GEC1/IO100PDB3
45	GEC0/IO100NDB3
46	GEB1/IO99PDB3
47	GEB0/IO99NDB3
48	GEA1/IO98PDB3
49	GEA0/IO98NDB3
50	VMV3
51	GNDQ
52	GND
53	NC
54	NC
55	GEA2/IO97RSB2
56	GEB2/IO96RSB2
57	GEC2/IO95RSB2
58	IO94RSB2
59	IO93RSB2
60	IO92RSB2
61	IO91RSB2
62	VCCIB2
63	IO90RSB2
64	IO89RSB2
65	GND
66	IO88RSB2
67	IO87RSB2
68	IO86RSB2
69	IO85RSB2
70	IO84RSB2
71	VCC
72	VCCIB2

PQ208	
Pin Number	A3P250 Function
73	IO83RSB2
74	IO82RSB2
75	IO81RSB2
76	IO80RSB2
77	IO79RSB2
78	IO78RSB2
79	IO77RSB2
80	IO76RSB2
81	GND
82	IO75RSB2
83	IO74RSB2
84	IO73RSB2
85	IO72RSB2
86	IO71RSB2
87	IO70RSB2
88	VCC
89	VCCIB2
90	IO69RSB2
91	IO68RSB2
92	IO67RSB2
93	IO66RSB2
94	IO65RSB2
95	IO64RSB2
96	GDC2/IO63RSB2
97	GND
98	GDB2/IO62RSB2
99	GDA2/IO61RSB2
100	GNDQ
101	TCK
102	TDI
103	TMS
104	VMV2
105	GND
106	VPUMP
107	NC
108	TDO

FG484	
Pin Number	A3P400 Function
E21	NC
E22	NC
F1	NC
F2	NC
F3	NC
F4	IO154VDB3
F5	IO155VDB3
F6	IO11RSB0
F7	IO07RSB0
F8	GAC0/IO04RSB0
F9	GAC1/IO05RSB0
F10	IO20RSB0
F11	IO24RSB0
F12	IO33RSB0
F13	IO39RSB0
F14	IO45RSB0
F15	GBC0/IO54RSB0
F16	IO48RSB0
F17	VMV0
F18	IO61NPB1
F19	IO63PDB1
F20	NC
F21	NC
F22	NC
G1	NC
G2	NC
G3	NC
G4	IO151VDB3
G5	IO151UDB3
G6	GAC2/IO153UDB3
G7	IO06RSB0
G8	GNDQ
G9	IO10RSB0
G10	IO19RSB0
G11	IO26RSB0
G12	IO30RSB0

FG484	
Pin Number	A3P400 Function
G13	IO40RSB0
G14	IO46RSB0
G15	GNDQ
G16	IO47RSB0
G17	GBB2/IO61PPB1
G18	IO53RSB0
G19	IO63NDB1
G20	NC
G21	NC
G22	NC
H1	NC
H2	NC
H3	VCC
H4	IO150PDB3
H5	IO08RSB0
H6	IO153VDB3
H7	IO152VDB3
H8	VMV0
H9	VCCIB0
H10	VCCIB0
H11	IO25RSB0
H12	IO31RSB0
H13	VCCIB0
H14	VCCIB0
H15	VMV1
H16	GBC2/IO62PDB1
H17	IO65RSB1
H18	IO52RSB0
H19	IO66PDB1
H20	VCC
H21	NC
H22	NC
J1	NC
J2	NC
J3	NC
J4	IO150NDB3

FG484	
Pin Number	A3P400 Function
J5	IO149NPB3
J6	IO09RSB0
J7	IO152UDB3
J8	VCCIB3
J9	GND
J10	VCC
J11	VCC
J12	VCC
J13	VCC
J14	GND
J15	VCCIB1
J16	IO62NDB1
J17	IO49RSB0
J18	IO64PPB1
J19	IO66NDB1
J20	NC
J21	NC
J22	NC
K1	NC
K2	NC
K3	NC
K4	IO148NDB3
K5	IO148PDB3
K6	IO149PPB3
K7	GFC1/IO147PPB3
K8	VCCIB3
K9	VCC
K10	GND
K11	GND
K12	GND
K13	GND
K14	VCC
K15	VCCIB1
K16	GCC1/IO67PPB1
K17	IO64NPB1
K18	IO73PDB1

Revision	Changes	Page
Revision 13 (January 2013)	The "ProASIC3 Ordering Information" section has been updated to mention "Y" as "Blank" mentioning "Device Does Not Include License to Implement IP Based on the Cryptography Research, Inc. (CRI) Patent Portfolio" (SAR 43104).	1-IV
	Added a note to Table 2-2 • Recommended Operating Conditions 1 (SAR 43644): The programming temperature range supported is $T_{\text{ambient}} = 0^{\circ}\text{C}$ to 85°C .	2-2
	The note in Table 2-115 • ProASIC3 CCC/PLL Specification referring the reader to SmartGen was revised to refer instead to the online help associated with the core (SAR 42569).	2-90
	Libero Integrated Design Environment (IDE) was changed to Libero System-on-Chip (SoC) throughout the document (SAR 40284). Live at Power-Up (LAPU) has been replaced with 'Instant On'.	NA
Revision 12 (September 2012)	The Security section was modified to clarify that Microsemi does not support read-back of programmed data.	1-1
	Added a Note stating "VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" section on page 3-1 for further information" to Table 2-1 • Absolute Maximum Ratings and Table 2-2 • Recommended Operating Conditions 1 (SAR 38321).	2-1 2-2
	Table 2-35 • Duration of Short Circuit Event Before Failure was revised to change the maximum temperature from 110°C to 100°C , with an example of six months instead of three months (SAR 37933).	2-31
	In Table 2-93 • Minimum and Maximum DC Input and Output Levels , VIL and VIH were revised so that the maximum is 3.6 V for all listed values of VCCI (SAR 28549).	2-68
	Figure 2-37 • FIFO Read and Figure 2-38 • FIFO Write are new (SAR 28371).	2-99
	The following sentence was removed from the "VMVx I/O Supply Voltage (quiet)" section in the "Pin Descriptions" chapter: "Within the package, the VMV plane is decoupled from the simultaneous switching noise originating from the output buffer VCCI domain" and replaced with "Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks" (SAR 38321). The datasheet mentions that "VMV pins must be connected to the corresponding VCCI pins" for an ESD enhancement.	3-1

Revision	Changes	Page
Advance v0.6 (continued)	The "Programming" section was updated to include information concerning serialization.	2-53
	The "JTAG 1532" section was updated to include SAMPLE/PRELOAD information.	2-54
	"DC and Switching Characteristics" chapter was updated with new information.	3-1
	The A3P060 "100-Pin VQFP" pin table was updated.	4-13
	The A3P125 "100-Pin VQFP" pin table was updated.	4-13
	The A3P060 "144-Pin TQFP" pin table was updated.	4-16
	The A3P125 "144-Pin TQFP" pin table was updated.	4-18
	The A3P125 "208-Pin PQFP" pin table was updated.	4-21
	The A3P400 "208-Pin PQFP" pin table was updated.	4-25
	The A3P060 "144-Pin FBGA" pin table was updated.	4-32
	The A3P125 "144-Pin FBGA" pin table is new.	4-34
	The A3P400 "144-Pin FBGA" is new.	4-38
	The A3P400 "256-Pin FBGA" was updated.	4-48
	The A3P1000 "256-Pin FBGA" was updated.	4-54
	The A3P400 "484-Pin FBGA" was updated.	4-58
	The A3P1000 "484-Pin FBGA" was updated.	4-68
	The A3P250 "100-Pin VQFP*" pin table was updated.	4-14
	The A3P250 "208-Pin PQFP*" pin table was updated.	4-23
	The A3P1000 "208-Pin PQFP*" pin table was updated.	4-29
	The A3P250 "144-Pin FBGA*" pin table was updated.	4-36
	The A3P1000 "144-Pin FBGA*" pin table was updated.	4-32
	The A3P250 "256-Pin FBGA*" pin table was updated.	4-45
	The A3P1000 "256-Pin FBGA*" pin table was updated.	4-54
	The A3P1000 "484-Pin FBGA*" pin table was updated.	4-68
Advance v0.5 (November 2005)	The "I/Os Per Package" table was updated for the following devices and packages: DevicePackage A3P250/M7ACP250VQ100 A3P250/M7ACP250FG144 A3P1000FG256	ii
Advance v0.4	M7 device information is new.	N/A
	The I/O counts in the "I/Os Per Package" table were updated.	ii
Advance v0.3	The "I/Os Per Package" table was updated.	ii
	M7 device information is new.	N/A
	Table 2-4 • ProASIC3 Globals/Spines/Rows by Device was updated to include the number or rows in each top or bottom spine.	2-16
	EXTFB was removed from Figure 2-24 • ProASIC3E CCC Options.	2-24



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